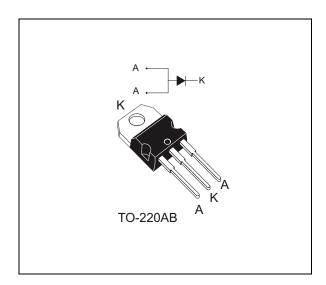


# **FERD30SM100S**

### Field effect rectifier

Datasheet - production data



### **Features**

- ST proprietary process
- Reduce leakage current
- Low forward voltage drop
- High frequency operation
- ECOPACK®2 compliant component

This is information on a product in full production.

## **Description**

The FERD30SM100S is based on a proprietary technology that achieves the best in class  $V_{\rm F}/I_{\rm R}$  trade-off for a given silicon surface.

This 100 V rectifier has been optimized for use in confined applications where both efficiency and thermal performance are key.

**Table 1. Device summary** 

Symbol	Value
I <sub>F(AV)</sub>	30 A
V <sub>RRM</sub>	100 V
T <sub>j</sub> (max)	+175 °C
V <sub>F</sub> (typ)	0.39 V

Characteristics FERD30SM100S

## 1 Characteristics

Table 2. Absolute ratings (limiting values, at 25 °C, unless otherwise specified, anode terminals short-circuited)

Symbol	Parameter	Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage		100	V
I <sub>F(RMS)</sub>	Forward rms current		60	Α
I <sub>F(AV)</sub>	Average forward current, $\delta = 0.5$ $T_c = 130  ^{\circ}\text{C}$		30	Α
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms}$ sinusoidal		250	А
T <sub>stg</sub>	Storage temperature range		-65 to + 175	°C
T <sub>j</sub> <sup>(1)</sup>	Maximum operating junction temperature		175	°C

<sup>1.</sup>  $\frac{dPtot}{dT_j} < \frac{1}{Rth(j-a)}$  condition to avoid thermal runaway for a diode on its own heatsink.

Table 3. Thermal resistance

Symbol	Parameter	Value (max)	Unit
R <sub>th(j-c)</sub>	Junction to case	1.6	°C/W

Table 4. Static electrical characteristics (anode terminals short-circuited)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
	I <sub>R</sub> <sup>(1)</sup> Reverse leakage current	T <sub>j</sub> = 25 °C	$V_R = V_{RRM}$	-	-	150	μΑ
I <sub>R</sub> <sup>(1)</sup>		T <sub>j</sub> = 125 °C		1	8	16	mA
		T <sub>j</sub> = 125 °C	V <sub>R</sub> = 70 V	-	-	9	ША
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 5 A	-	-	0.475	
		T <sub>j</sub> = 125 °C		-	0.39	0.43	
V <sub>E</sub> <sup>(2)</sup>	Forward valtage drap	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 10A	-	-	0.585	V
V <sub>F</sub> Forward vo	Forward voltage drop	T <sub>j</sub> = 125 °C		-	0.50	0.545	V
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 30 A	-		0.95	
		T <sub>j</sub> = 125 °C		-	0.64	0.71	

<sup>1.</sup> Pulse test:  $t_p = 5$  ms,  $\delta < 2\%$ 

To evaluate the conduction losses use the following equation:

$$P = 0.56 \times I_{F(AV)} + 0.005 I_{F^{2}(RMS)}$$



<sup>2.</sup> Pulse test:  $t_p$  = 380  $\mu$ s,  $\delta$  < 2%

FERD30SM100S Characteristics

Figure 1. Average forward power dissipation versus average forward current

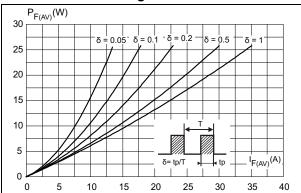


Figure 2. Average forward current versus ambient temperature ( $\delta = 0.5$ )

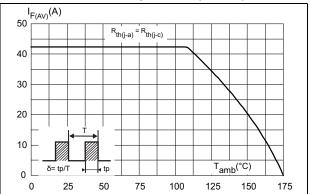
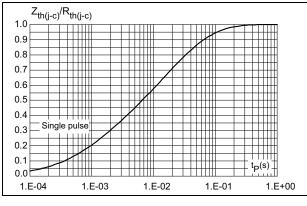


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Reverse leakage current versus reverse voltage applied (typical values)



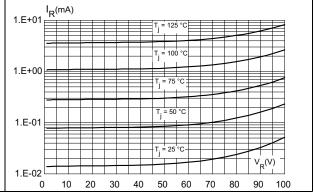
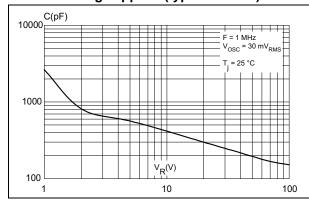
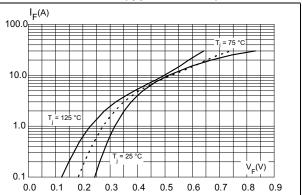


Figure 5. Junction capacitance versus reverse voltage applied (typical values)

Figure 6. Forward voltage drop versus forward current (typical values)





#### 2 **Package information**

Epoxy meets UL94, V0

Cooling method: by conduction (C)

Recommended torque value: 0.55 N·m

Maximum torque value: 0.77 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Ε  $\varnothing P$ Resin gate 0.5 mm max. protrusion(1) Q H1 D D1 L30 L20 b1 L1 Resin gate С 0.5 mm max. protrusion(1) (1) Resin gate position accepted in each of the two position shown as well as the symmetrical opposites

Figure 7. TO-220AB dimension definitions



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FERD30SM100S Package information

Table 5. TO-220AB dimension values

	Dimensions					
Ref.	Millin	neters	Inches			
	Min.	Max.	Min.	Max.		
А	4.40	4.60	0.17	0.18		
b	0.61	0.88	0.024	0.035		
b1	1.14	1.70	0.045	0.067		
С	0.48	0.70	0.019	0.027		
D	15.25	15.75	0.60	0.62		
D1	1.27 typ.		0.05	typ.		
Е	10	10.40	0.39	0.41		
е	2.40	2.70	0.094	0.106		
e1	4.95	5.15	0.19	0.20		
F	1.23	1.32	0.048	0.052		
H1	6.20	6.60	0.24	0.26		
J1	2.40	2.72	0.094	0.107		
L	13	14	0.51	0.55		
L1	3.50	3.93	0.137	0.154		
L20	16.40 typ.		0.64 typ.			
L30	28.90 typ.		1.13 typ.			
ØP	3.75	3.85	0.147	0.151		
Q	2.65	2.95	0.104	0.116		



Ordering information FERD30SM100S

# **3** Ordering information

**Table 6. Ordering information** 

Order code	Marking	Package	Weight	Base qty	Delivery mode
FERD30SM100ST	FERD30SM100ST	TO-220AB	1.9 g	50	Tube

# 4 Revision history

Table 7. Document revision history

Date	Revision	Changes
12-Jan-2015	1	Initial release.

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